

European Workshop on Refractory Metals and Silicides Slated for March 1989

A European Workshop on Refractory Metals and Silicides is scheduled for March 20-22, 1989 in Houthalen, Belgium. The workshop is being organized by the Interuniversity Microelectronics Center (IMEC), Louvain, Belgium, as a residential program at the Hengelhoeef conference complex. It follows a successful 1987 workshop organized by the Centre National d'Études des Télécommunications (CNET, Meylan, France) on the same subject.

The 1989 workshop will cover a variety of subjects dealing with refractory metals and silicides, including fundamental studies, deposition and formation techniques, film properties, VLSI process-related aspects, and novel applications. Papers will also be presented on device aspects dealing with contacts and interconnects for both silicon and compound semiconductors. Invited papers will be scheduled as lead-off presentations to the subjects of the regular sessions. There will be both oral and poster contributions.

Members of the scientific committee include: G. Bomchil (CNET, Meylan, France), R. De Keersmaecker (IMEC, Louvain, Belgium), K. Hieber (Siemens, Munich, W. Germany), P. Huggett (Plessey Research, Caswell, U.K.), R. Madar (CNRS, Grenoble, France), G. Ottaviani (University of Modena, Italy), S. Petersson (Royal Institute of Technology, Stockholm, Sweden), I. Suni (Technological Research Center, Espoo, Finland), W. van der Weg (State University, Utrecht, Netherlands), M. van Rossum (IMEC, Louvain, Belgium), and C. Werkhoven (Philips, Eindhoven, Netherlands).

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Third Session of European School on III-V Compound Microelectronics Will Be Held in October

The third session of the European School on High Speed Digital and Microwave GaAs Integrated Circuits and Optoelectronic Systems will be held October 10-19, 1988 in Paris, XI/Orsay and Bordeaux. Topics to be covered in this session include high speed signal processing GaAs, digital full USTOM and standard cells, CAD, fast analog-to-digital converters, monolithic microwave integrated circuit design and characterization, op-

toelectronic devices and interface systems and reverse engineering, failure analysis of GaAs, integrated circuits, qualification and testing.

This session completes a series of three independent but correlated sessions of theoretical and practical courses and laboratory visits organized by Euroforum, an organization of the European Economic Community. The first session, held May 9-13, 1988 in Madrid, dealt with the electronic and optical properties of III-V materials, characterization techniques, and the basic physics of advanced devices. The second session, held June 20-24 in Aachen, discussed advanced devices and IC technologies, MOVPE and MBE equipment, growth of thin films, dielectric film deposition and characterization, submicron lithography, and dry etching.

For further information contact: A.M. Ruiz Jimenez (Spain), telephone 341 80 71 613; H. Henke (W. Germany), telephone 49 241 80 77 50; or S. Rigo (France), telephone (1) 69 41 72 66.

SIMOX Workshop To Be Held at University of Surrey

A two-day workshop on SIMOX materials will be held at the University of Surrey, England, on November 7-8, 1988 under the auspices of the Council of the European Community. The event will mark the conclusion of a successful two-year program funded by the CEC. Because of the current high level of interest in this technology, the scope of the meeting was widened to include many aspects of SIMOX materials that are of interest to the silicon-on-insulator community.

The workshop will be structured around the following themes, introduced by invited keynote speakers and followed by roundtable discussions: oxide layer growth, causes and control of defects in the silicon overlayer, contamination and dopant activity, thermal donors and new donors, nondestructive testing/quality control, and device issues. The closing session will look to the future by covering such issues as problem areas, second gen-

eration machines, and the possibility of international collaborative experiments. Papers will be published in a conference proceedings.

For information contact: Mrs. Brenda Dore, SIMOX Workshop Secretary, Department of Electronic and Electrical Engineering, University of Surrey, Guildford, Surrey GU2 5XH, United Kingdom; telephone (0483) 571281, ext. 2270; fax (0483) 300803.

NATO Workshop Scheduled on Computer Modeling in Crystal Growth To Be Held in Conjunction With Crystal Growth Conference

The NATO Workshop on Computer Modeling in Crystal Growth from the Melt will take place in conjunction with the Crystal Growth Conference of the Italian (AICC) and German (DGKK) crystal growth associations to be held in Parma, Italy, April 4-6, 1989. The NATO workshop, which will also have semiconductor growth as one of its main topics, will cover:

- Numerical modeling in growth of III-V compounds, with work on silicon included where it is relevant for the growth of materials;
- Modeling of convective effects in Czochralski and Bridgman configurations;
- Modeling of the action of magnetic fields in melt growth;
- Calculation of thermal stress and dislocation formation in melt growth; and
- Numerical modeling of transport effects on stoichiometry, segregation, etc. in III-V bulk growth.

All invited and contributed papers will be published in the Springer-Verlag series on crystals.

For information contact: Priv. Doz. Dr. G. Müller, Institut für Werkstoffwissenschaften 6, Martensstrasse 7, D-8520 Erlangen, W. Germany. □

1988 E-MRS Fall Meeting

November 7-10, 1988

Strasbourg, France

See Calendar listing in this issue.